www.ti.com

LF147/LF347 Wide Bandwidth Quad JFET Input Operational Amplifiers

Check for Samples: LF147, LF347-N

FEATURES

Internally Trimmed Offset Voltage: 5 mV max

Low Input Bias Current: 50 pA

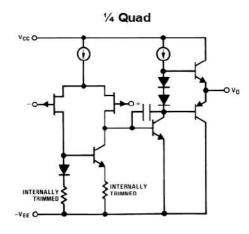
Low Input Noise Current: 0.01 pA/√Hz

Wide Gain Bandwidth: 4 MHz
 High Slew Rate: 13 V/μs
 Low Supply Current: 7.2 mA
 High Input Impedance: 10¹²Ω

Low Total Harmonic Distortion: ≤0.02%

Low 1/f Noise Corner: 50 Hz
 Fast Settling Time to 0.01%: 2 μs

Simplified Schematic

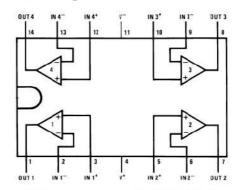


DESCRIPTION

The LF147 is a low cost, high speed quad JFET input operational amplifier with an internally trimmed input offset voltage (BI-FET II™ technology). The device requires a low supply current and yet maintains a large gain bandwidth product and a fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF147 is pin compatible with the standard LM148. This feature allows designers to immediately upgrade the overall performance of existing LF148 and LM124 designs.

The LF147 may be used in applications such as high speed integrators, fast D/A converters, sample-and-hold circuits and many other circuits requiring low input offset voltage, low input bias current, high input impedance, high slew rate and wide bandwidth. The device has low noise and offset voltage drift.

Connection Diagram



LF147 available as per JM38510/11906.

Figure 1. 14-Pin PDIP / CDIP / SOIC Top View See Package Number J0014A, D0014A or NFF0014A

A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

BI-FET II is a trademark of dcl_owner.

All other trademarks are the property of their respective owners.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

Absolute Maximum Ratings (1)(2)

			LF147	LF347B/LF347
Supply Voltage			±22V	±18V
Differential Input Voltage			±38V	±30V
Input Voltage Range (3)			±19V	±15V
Output Short Circuit Duratio	on ⁽⁴⁾		Continuous	Continuous
Power Dissipation (5) (6)			900 mW	1000 mW
T _i max	150°C	150°C		
θ_{jA}	CDIP (J) Package		70°C/W	
	PDIP (NFF) Package		75°C/W	
	SOIC Narrow (D)		100°C/W	
	SOIC Wide (D)		*	85°C/W
Operating Temperature Ra	nge		See (7)	See (7)
Storage Temperature Rang	je		-65°C:	≤T _A ≤150°C
Lead Temperature (Solderi	ng, 10 sec.)		260°C	260°C
Soldering Information	PDIP / CDIP	Soldering (10 seconds)		260°C
	SOIC Package	Vapor Phase (60 seconds)		215°C
	Control of	Infrared (15 seconds)		220°C
ESD Tolerance (8)	1.	**		900V

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not ensure specific performance limits.
- If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.
- Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.
- (4) Any of the amplifier outputs can be shorted to ground indefinitely, however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.
- For operating at elevated temperature, these devices must be derated based on a thermal resistance of θ_{jA} .

 Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside ensured limits.
- The LF147 is available in the military temperature range -55°C≤T_A≤125°C, while the LF347B and the LF347 are available in the commercial temperature range 0°C≤T_A≤70°C. Junction temperature can rise to T_i max = 150°C.
- Human body model, 1.5 kΩ in series with 100 pF

DC Electrical Characteristics (1)(2)

Symbol	Parameter	Conditions		LF147	7	LF347B			LF347			Units
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Vos	Input Offset Voltage	R _S =10 kΩ, T _A =25°C		1	5		3	5		5	10	mV
	1000	Over Temperature			8			7			13	mV
ΔV _{OS} /Δ Τ	Average TC of Input Offset Voltage	R _S =10 kΩ		10			10			10		μV/°C
los	Input Offset Current	T _j =25°C, ^{(2) (3)} Over Temperature		25	100 25		25	100 4		25	100 4	pA nA
I _B	Input Bias Current	T _j =25°C, ^{(2) (3)} Over Temperature		50	200 50		50	200 8		50	200 8	pА пА
R _{IN}	Input Resistance	T _j =25°C		10 ¹²			10 ¹²			10 ¹²		Ω

- (1) Refer to RETS147X for LF147D and LF147J military specifications.
- Unless otherwise specified the specifications apply over the full temperature range and for V_S=±20V for the LF147 and for V_S=±15V for the LF347B/LF347. Vos. IB, and Ios are measured at VcM=0.
- The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature. Ti. Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, P_D . $T_j = T_A + \theta_{jA}$ P_D where θ_{jA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

Submit Documentation Feedback

Copyright © 1999-2013, Texas Instruments Incorporated

www.ti.com

DC Electrical Characteristics (1)(2) (continued)

Symbol	Parameter	Conditions		LF147	7		LF347E	3		Units		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
A _{VOL}	Large Signal Voltage Gain	V _O =±10V, R _L =2 kΩ	50	100		50	100		25	100		V/mV
		Over Temperature	25			25			15			V/mV
Vo	Output Voltage Swing	$V_S=\pm 15V$, $R_L=10$ $k\Omega$	±12	±13.		±12	±13.		±12	±13. 5		V
V _{CM}	Input Common-Mode Voltage Range	V _S =±15V	±11	+15 -12		±11	+15 -12		±11	+15 -12		V V
CMRR	Common-Mode Rejection Ratio	R _S ≤10 kΩ	80	100		80	100		70	100		dB
PSRR	Supply Voltage Rejection Ratio	See (4)	80	100		80	100		70	100		dB
Is	Supply Current			7.2	11		7.2	11		7.2	11	mA

⁽⁴⁾ Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously in accordance with common practice from V_S = ±5V to ±15V for the LF347 and LF347B and from V_S = ±20V to ±5V for the LF147.

AC Electrical Characteristics (1)(2)

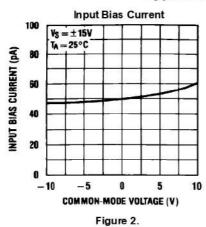
Symbol	Parameter	Conditions		LF147	7	LF347B			LF347			Units
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
	Amplifier to Amplifier Coupling	T _A =25°C, f=1 Hz-20 kHz (Input Referred)		-120			-120			-120		dB
SR	Slew Rate	V _S =±15V, T _A =25°C	8	13		8	13		8	13		V/µs
GBW	Gain-Bandwidth Product	V _S =±15V, T _A =25°C	2.2	4		2.2	4		2.2	4		MHz
e _n	Equivalent Input Noise Voltage	T_A =25°C, R_S =100 Ω , f=1000 Hz		20			20		20			nV / √Hz
in	Equivalent Input Noise Current	T _j =25°C, f=1000 Hz		0.01			0.01			0.01		pA / √Hz
THD				<0.0 2			<0.0 2			<0.0 2		%

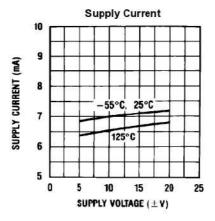
⁽¹⁾ Unless otherwise specified the specifications apply over the full temperature range and for $V_S=\pm20V$ for the LF147 and for $V_S=\pm15V$ for the LF347B/LF347. V_{OS}, I_B, and I_{OS} are measured at V_{CM}=0.

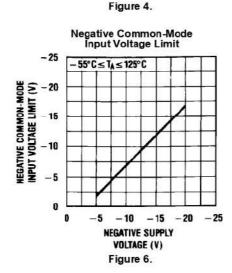
(2) Refer to RETS147X for LF147D and LF147J military specifications.

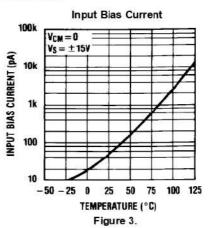


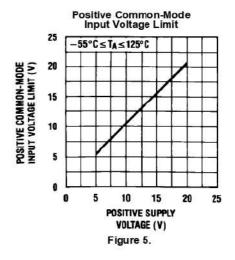
Typical Performance Characteristics

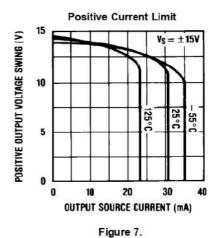






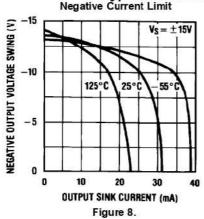


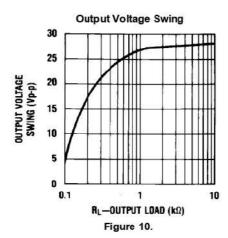


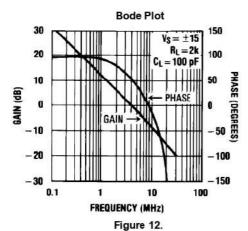


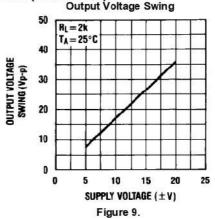


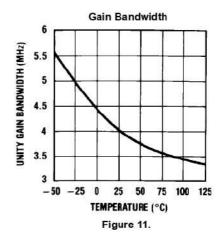
Typical Performance Characteristics (continued) Negative Current Limit Output Voltage Swing

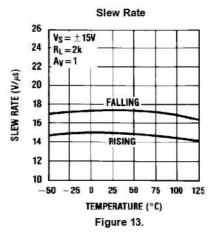














Typical Performance Characteristics (continued)

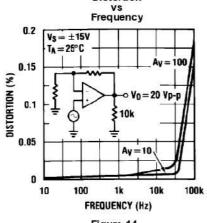
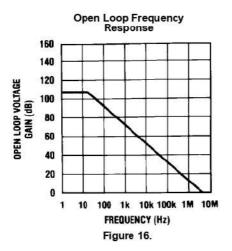
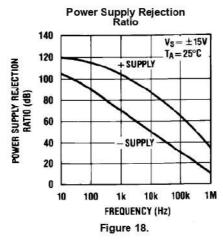


Figure 14.





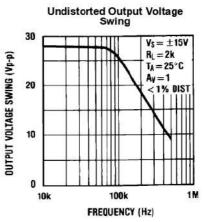
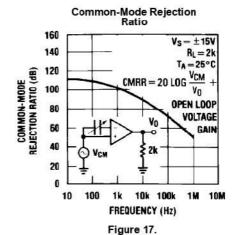
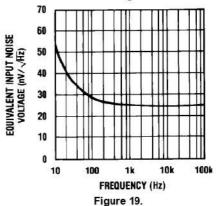


Figure 15.

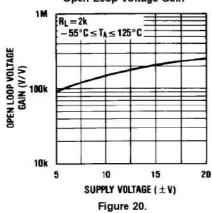


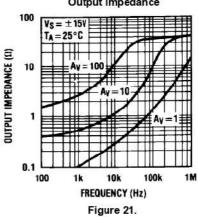
Equivalent Input Noise Voltage

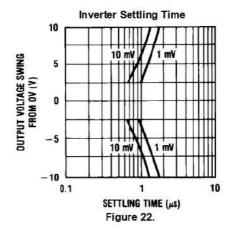




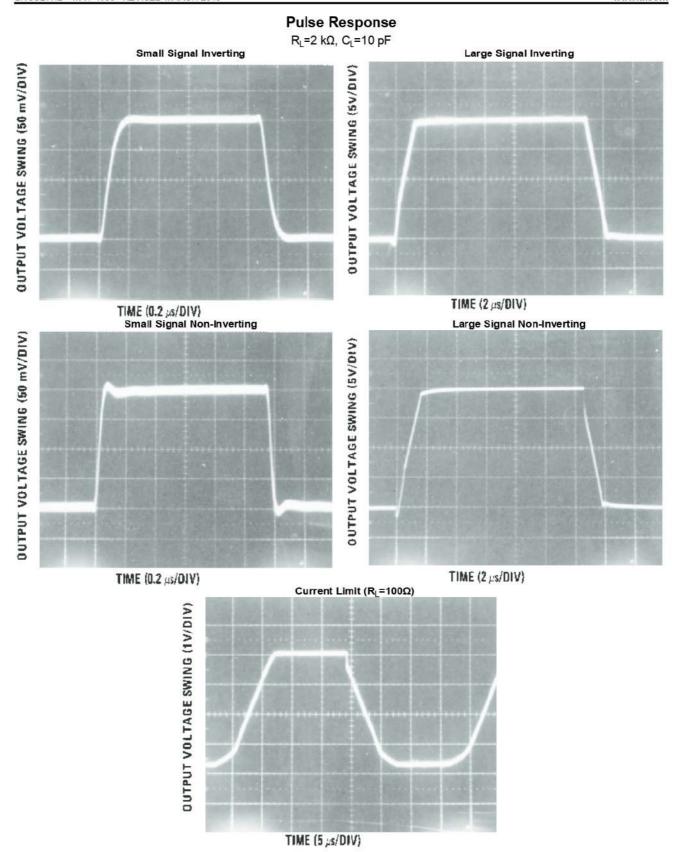
Typical Performance Characteristics (continued) Open Loop Voltage Gain Output Impedance













APPLICATION HINTS

The LF147 is an op amp with an internally trimmed input offset voltage and JFET input devices (BI-FET II). These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output; however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

The amplifiers will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

Each amplifier is individually biased by a zener reference which allows normal circuit operation on ±4.5V power supplies. Supply voltages less than these may result in lower gain bandwidth and slew rate.

The LF147 will drive a 2 $k\Omega$ load resistance to ±10V over the full temperature range. If the amplifier is forced to drive heavier load currents, however, an increase in input offset voltage may occur on the negative voltage swing and finally reach an active current limit on both positive and negative swings.

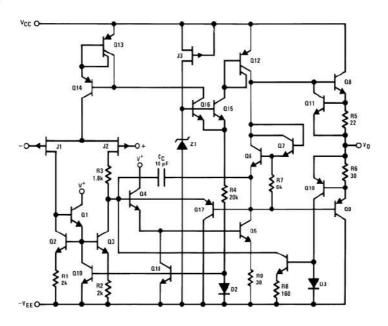
Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.



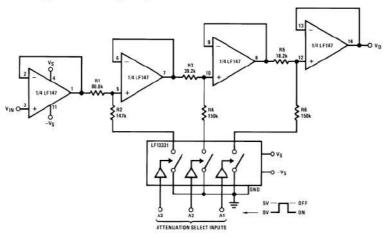
Detailed Schematic





Typical Applications

Figure 23. Digitally Selectable Precision Attenuator



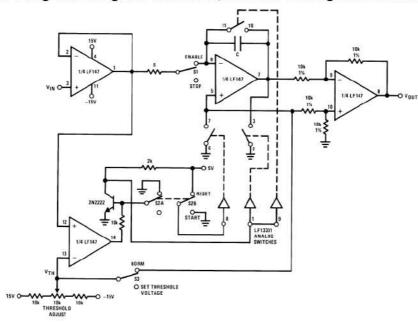
All resistors 1% tolerance

- Accuracy of better than 0.4% with standard 1% value resistors No offset adjustment necessary
- · Expandable to any number of stages
- · Very high input impedance

A1	A2	A3	v _o
			Attenuation
0	0	0	0
0	0	1	-1 dB
0	1	0	−2 dB
0	1	1	−3 dB
1	0	0	-4 dB
1	0	1	−5 dB
1	1	0	−6 dB
1	1	1	-7 dB



Figure 24. Long Time Integrator with Reset, Hold and Starting Threshold Adjustment

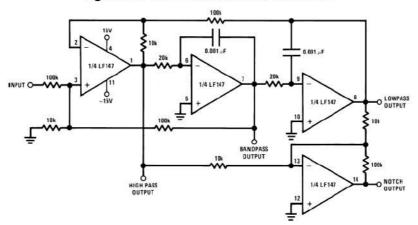


V_{OUT} starts from zero and is equal to the integral of the input voltage with respect to the threshold voltage:

$$V_{OUT} = \frac{1}{RC} \int_{0}^{1} (V_{IN} - V_{TH}) dt$$

- Output starts when V_{IN}≥V_{TH}
- · Switch S1 permits stopping and holding any output value
- Switch S2 resets system to zero

Figure 25. Universal State Variable Filter



For circuit shown:

fo=3 kHz, fNOTCH=9.5 kHz

Q=3.4

Passband gain:

Highpass-0.1

Bandpass—1

Lowpass—1 Notch—10

- f₀×Q≤200 kHz
- 10V peak sinusoidal output swing without slew limiting to 200 kHz
- See LM148 data sheet for design equations

Submit Documentation Feedback



www.ti.com



REVISION HISTORY

С	nanges from Revision C (March 2013) to Revision D	Page
•	Changed layout of National Data Sheet to TI format	



PACKAGE OPTION ADDENDUM

1-Nov-2013

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing		Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (45)	Samples
LF147J	ACTIVE	CDIP	J	14	25	TBD	Call TI	Call TI	-55 to 125	LF147J	Samples
LF347BN/NOPB	ACTIVE	PDIP	NFF	14	25	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LF347BN	Samples
LF347BN/PB	NRND	PDIP	NEF	14	25	TBD	Call TI	Call TI		LF347BN	
LF347M	NRND	SOIC	D	14	55	TBD	Call TI	Call TI	0 to 70	LF347M	
LF347M/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LF347M	Samples
LF347MX	NRND	SOIC	D	14	2500	TBD	Call TI	Call TI	0 to 70	LF347M	
LF347MX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LF347M	Samples
LF347N/NOPB	ACTIVE	PDIP	NFF	14	25	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LF347N	Samples
LF347N/PB	NRND	PDIP	NFF	14	25	TBD	Call TI	Call TI		LF347N	

(1) The marketing status values are defined as follows: ACTIVE: Product device recommended for new designs. LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(P) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent.for the latest availability

¹⁴⁷ Eo Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent.for.the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): Ti's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, Ti Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exempt) for or either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): Til defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous materials).

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

1-Nov-2013

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

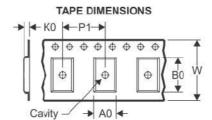
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 26-Mar-2013

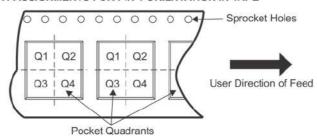
TAPE AND REEL INFORMATION

Reel Diameter Reel Diameter Reel Width (W1)



A0	Dimension designed to accommodate the component width
BO	Dimension designed to accommodate the component length
KO	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



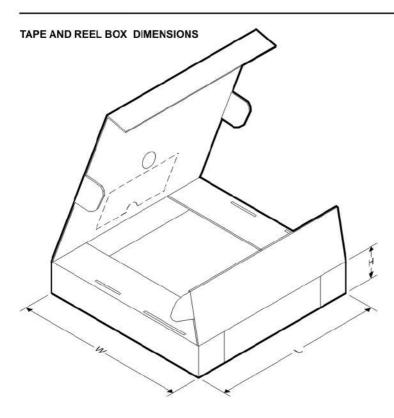
*All dimensions are nominal

Device	Package Type	Package Drawing	0.0000000000000000000000000000000000000	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LF347MX	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LF347MX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1



PACKAGE MATERIALS INFORMATION

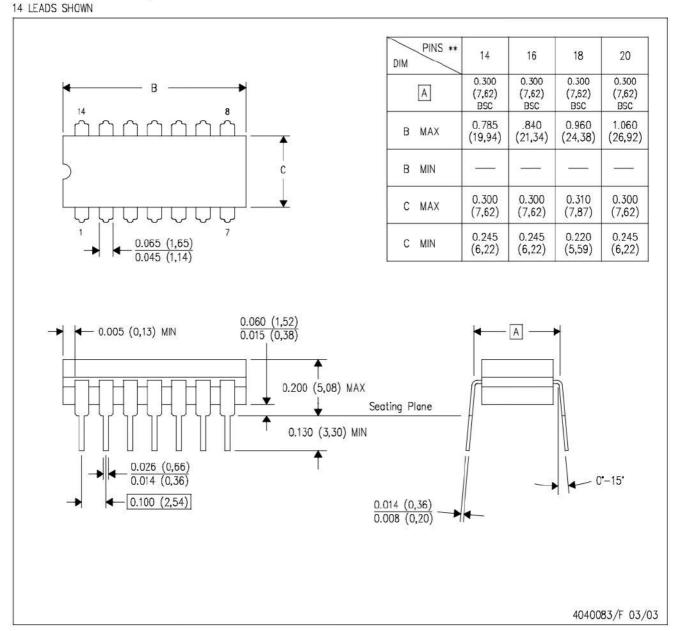
www.ti.com 26-Mar-2013



*All dimensions are nominal

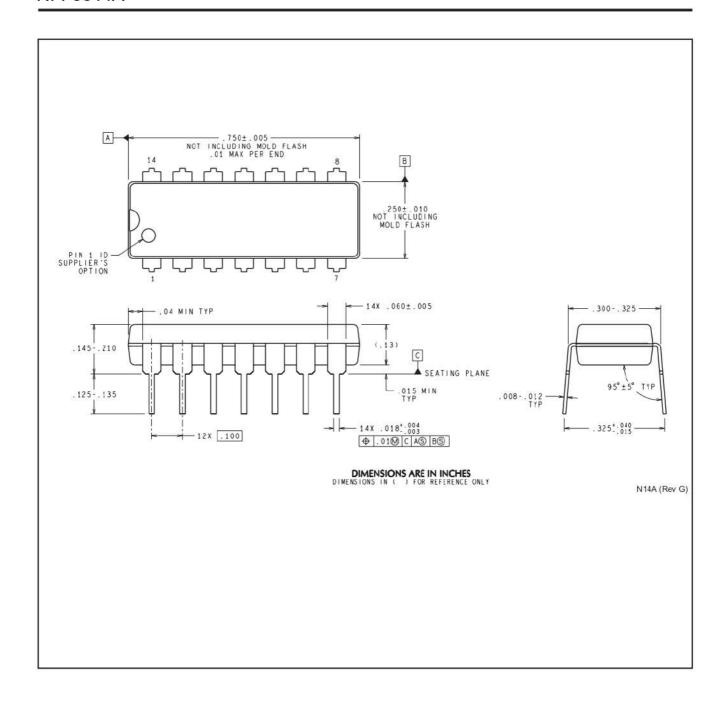
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LF347MX	SOIC	D	14	2500	367.0	367.0	35.0
LF347MX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0

U	14-	-GDIP-	- **
2000			,



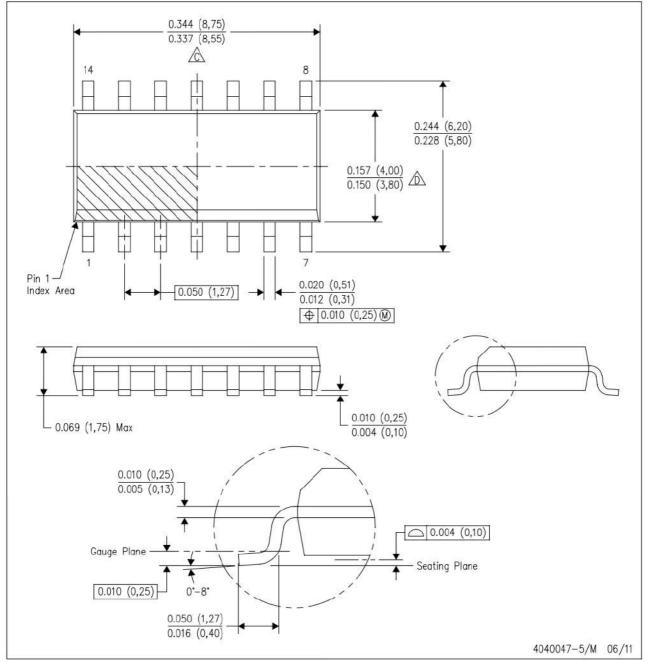
NOTES:

- A. All linear dimensions are in inches (millimeters).
- This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side. E. Reference JEDEC MS—012 variation AB.

